

General Description

The AO4813 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

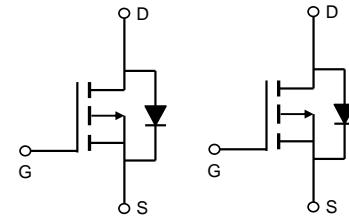
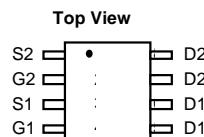
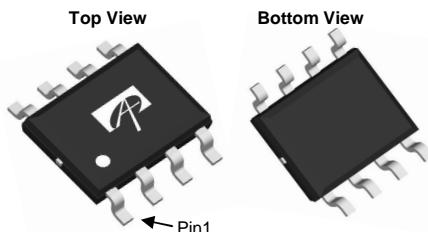
Product Summary

V_{DS}	-30V
I_D (at $V_{GS}=-10V$)	-7.1A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	< 25mΩ
$R_{DS(ON)}$ (at $V_{GS} = -4.5V$)	< 40mΩ

100% UIS Tested
100% R_g Tested



SOIC-8



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-7.1	A
Current $T_A=70^\circ C$		-5.6	
Pulsed Drain Current ^C	I_{DM}	-40	
Avalanche Current ^C	I_{AS}, I_{AR}	-27	A
Avalanche energy $L=0.1mH$ ^C	E_{AS}, E_{AR}	36	mJ
Power Dissipation ^B	P_D	2	W
Power Dissipation $T_A=70^\circ C$		1.3	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A $t \leq 10s$	$R_{\theta JA}$	48	62.5	°C/W
Maximum Junction-to-Ambient ^{A,D} Steady-State		74	90	°C/W
Maximum Junction-to-Lead	$R_{\theta JL}$	32	40	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-30\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}= \pm 20\text{V}$			± 100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-1.5	-2.0	-2.5	V
$I_{\text{D(ON)}}$	On state drain current	$V_{GS}=-10\text{V}, V_{DS}=-5\text{V}$	-40			A
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}, I_D=-7.1\text{A}$ $T_J=125^\circ\text{C}$		17 24	25 33	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}, I_D=-5.6\text{A}$		27	40	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-7.1\text{A}$		24		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$		-0.75	-1	V
I_S	Maximum Body-Diode Continuous Current				-2.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1\text{MHz}$		1040	1250	pF
C_{oss}	Output Capacitance			180		pF
C_{rss}	Reverse Transfer Capacitance			125	175	pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$	2	4	6	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, I_D=-7.1\text{A}$		19		nC
$Q_g(4.5\text{V})$	Total Gate Charge			9.6		nC
Q_{gs}	Gate Source Charge			3.6		nC
Q_{gd}	Gate Drain Charge			4.6		nC
$t_{\text{D(on)}}$	Turn-On DelayTime	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, R_L=2.2\Omega, R_{\text{GEN}}=3\Omega$		10		ns
t_r	Turn-On Rise Time			5.5		ns
$t_{\text{D(off)}}$	Turn-Off DelayTime			26		ns
t_f	Turn-Off Fall Time			9		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-7.1\text{A}, dI/dt=500\text{A}/\mu\text{s}$		11.5		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-7.1\text{A}, dI/dt=500\text{A}/\mu\text{s}$		25		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(\text{MAX})}=150^\circ\text{C}$, using $\leq 10\text{s}$ junction-to-ambient thermal resistance.

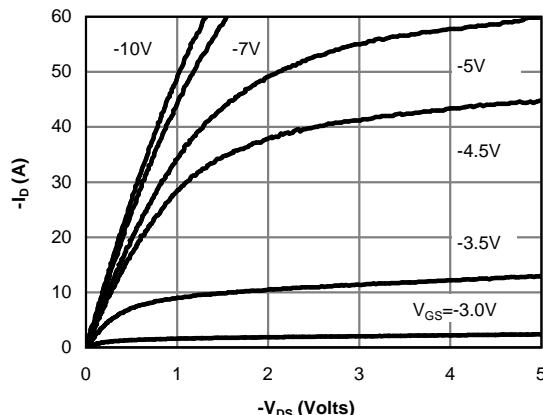
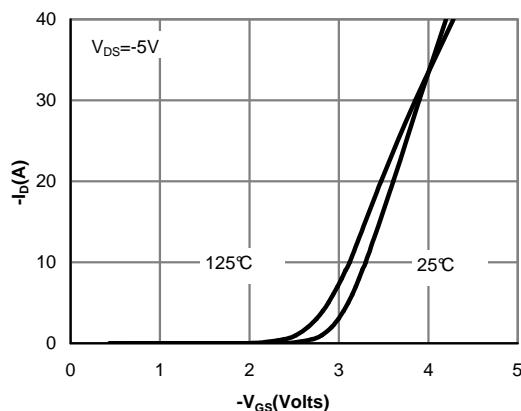
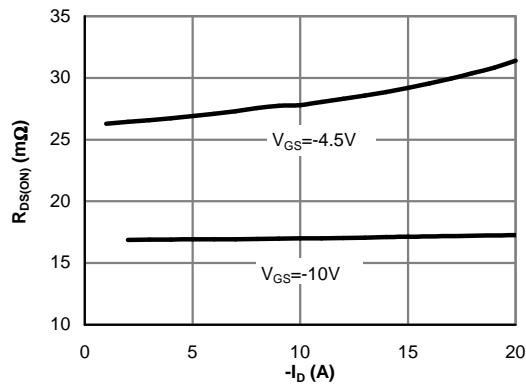
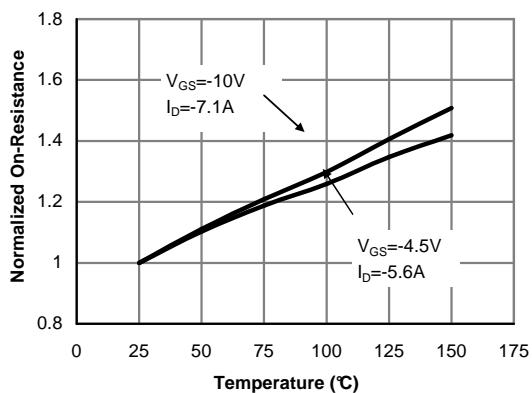
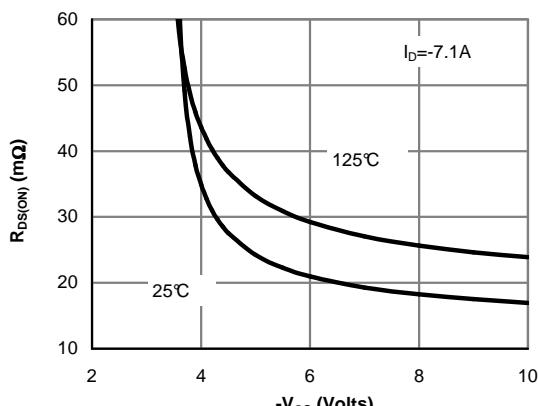
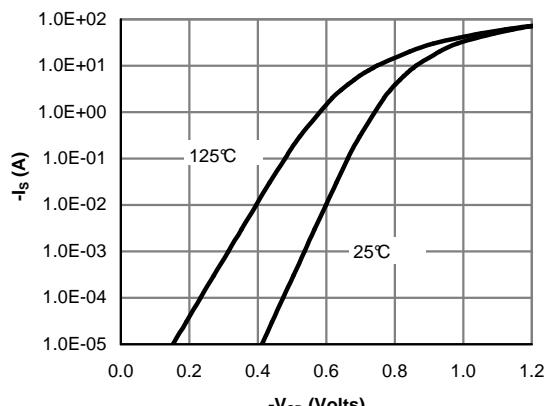
C. Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

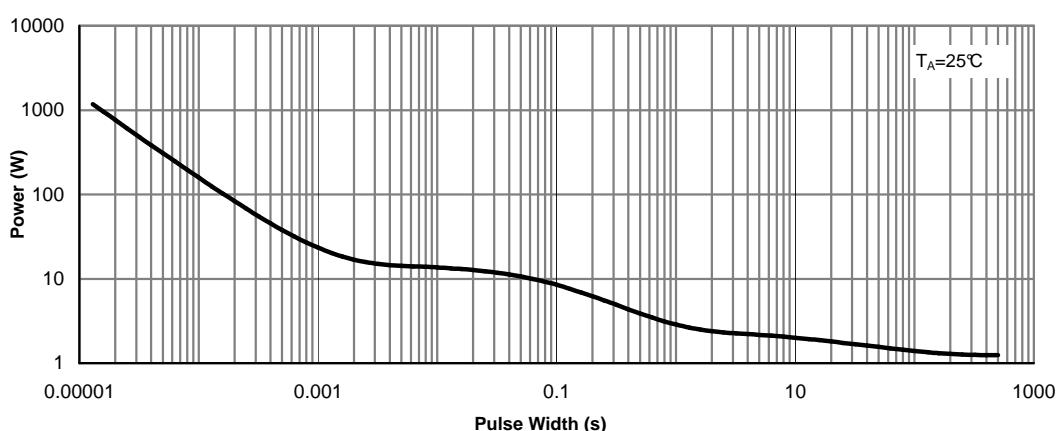
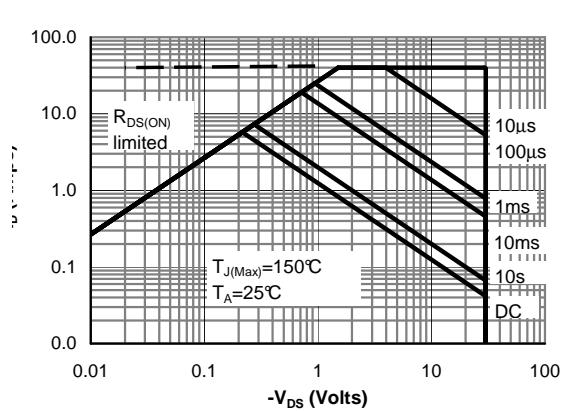
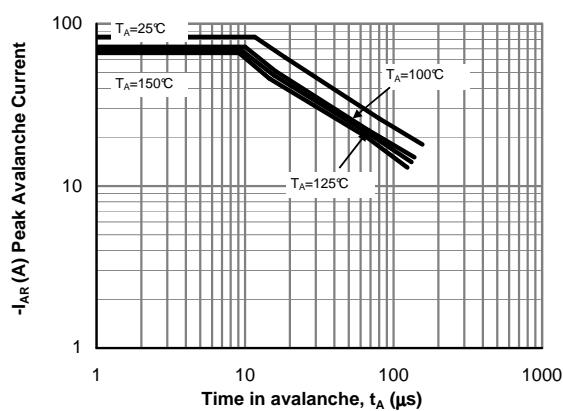
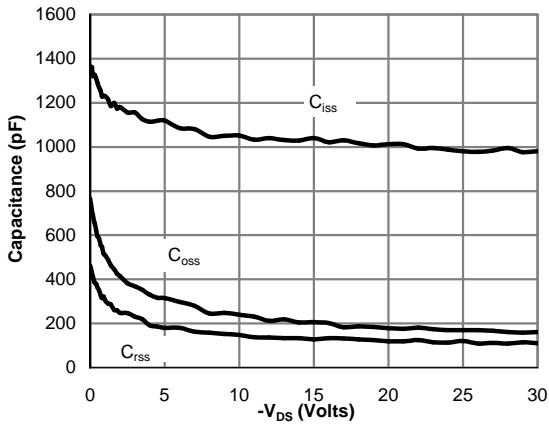
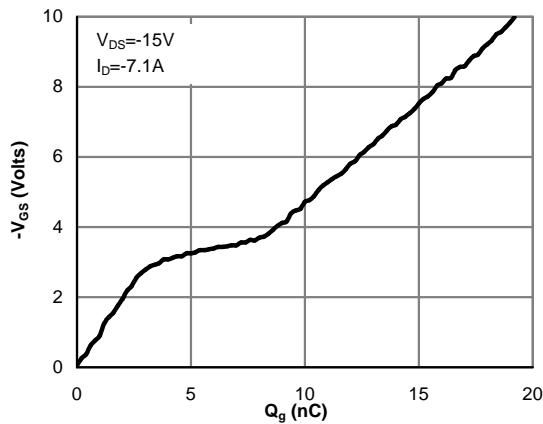
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(\text{MAX})}=150^\circ\text{C}$. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Fig 1: On-Region Characteristics (Note E)

Figure 2: Transfer Characteristics (Note E)

Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

Figure 4: On-Resistance vs. Junction Temperature (Note E)

Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS


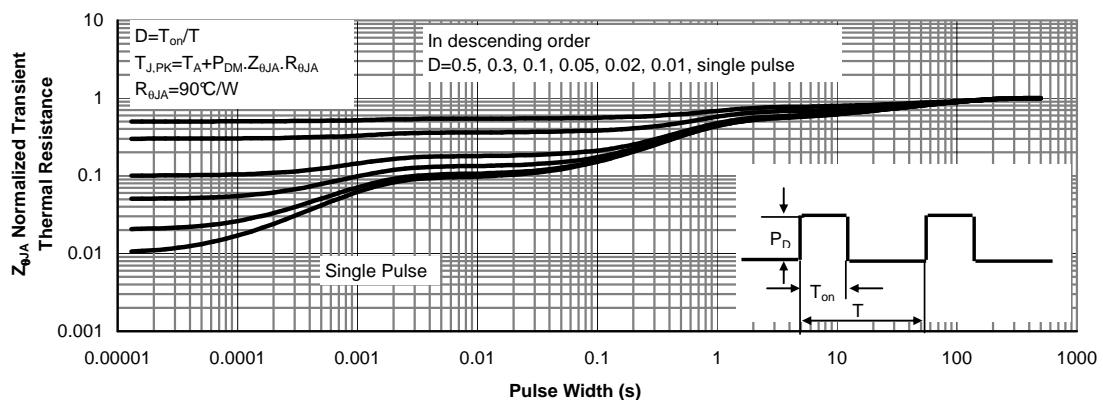
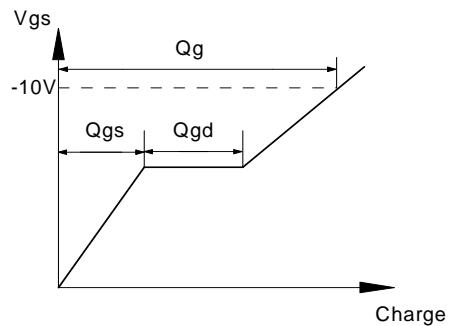
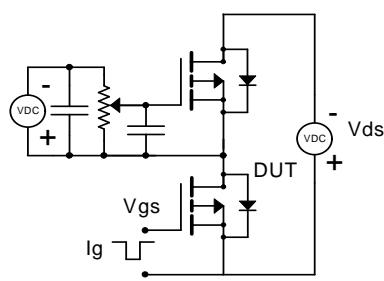
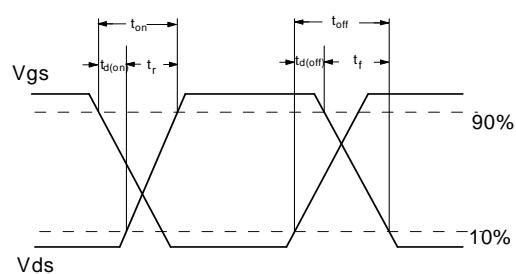
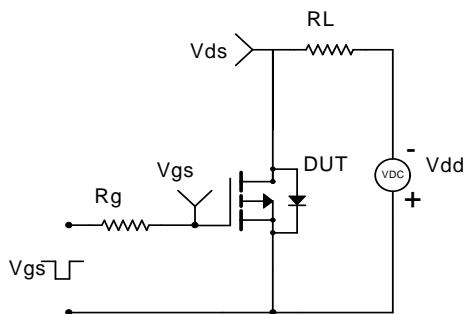
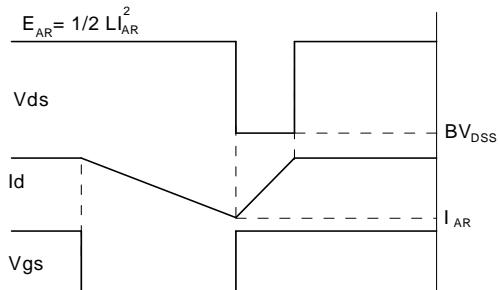
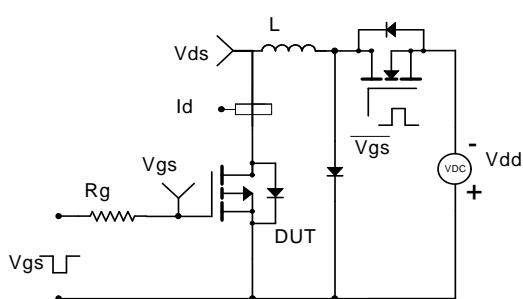
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveforms

Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

Diode Recovery Test Circuit & Waveforms
